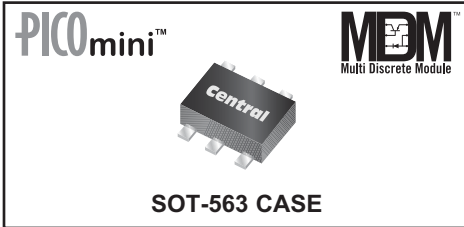


CMLM0305T
MULTI DISCRETE MODULE™
SURFACE MOUNT
N-CHANNEL MOSFET AND
LOW V_F SILICON SCHOTTKY DIODE



www.centrasemi.com



* Device is **Halogen Free** by design

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLM0305T is a Multi Discrete Module™ consisting of a single N-Channel Enhancement-mode MOSFET and a Low V_F Schottky diode packaged in a space saving PICOmini™ SOT-563 surface mount case. This device is designed for small signal general purpose applications where size and operational efficiency are prime requirements.

MARKING CODE: C35

APPLICATIONS:

- DC / DC Converters
- Battery Powered Portable Equipment

FEATURES:

- ESD protection up to 2kV
- Low r_{DS(on)} Transistor (1.5Ω MAX @ V_{GS}=5.0V)
- Low V_F Schottky Diode (0.47V MAX @ 0.5A)

MAXIMUM RATINGS - CASE: (T_A=25°C)

Power Dissipation (Note 1)	
Power Dissipation (Note 2)	
Power Dissipation (Note 3)	
Operating and Storage Junction Temperature	
Thermal Resistance	

SYMBOL		UNITS
P _D	350	mW
P _D	300	mW
P _D	150	mW
T _J , T _{stg}	-65 to +150	°C
θ _{JA}	357	°C/W

MAXIMUM RATINGS - Q1: (T_A=25°C)

Drain-Source Voltage	
Drain-Gate Voltage	
Gate-Source Voltage	
Continuous Drain Current	
Maximum Pulsed Drain Current	

SYMBOL		UNITS
V _{DS}	50	V
V _{DG}	50	V
V _{GS}	12	V
I _D	280	mA
I _{DM}	1.5	A

MAXIMUM RATINGS - D1: (T_A=25°C)

Peak Repetitive Reverse Voltage	
Continuous Forward Current	
Peak Repetitive Forward Current, tp≤1.0ms	
Peak Forward Surge Current, tp=8.0ms	

SYMBOL		UNITS
V _R RM	40	V
I _F	500	mA
I _{FRM}	3.5	A
I _{FSM}	10	A

ELECTRICAL CHARACTERISTICS - Q1: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{GSSF} , I _{GSSR}	V _{GS} =5.0V		50	nA
I _{GSSF} , I _{GSSR}	V _{GS} =10V		0.5	μA
I _{GSSF} , I _{GSSR}	V _{GS} =12V		1.0	μA
I _{DSS}	V _{DS} =50V, V _{GS} =0		50	nA
BV _{DSS}	V _{GS} =0, I _D =10μA	50		V
V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.75	1.2	V

- Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm²
(2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm²
(3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm²

R2 (18-January 2010)

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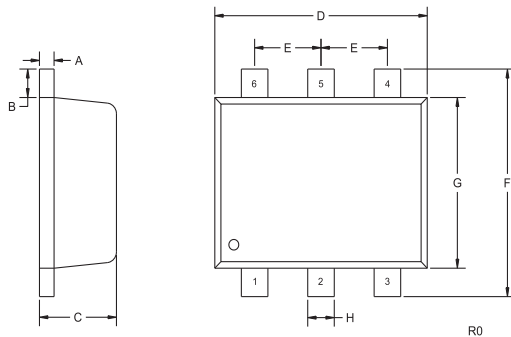
ELECTRICAL CHARACTERISTICS - Q1 - Continued:

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V _{SD}	V _{GS} =0, I _S =115mA			1.4	V
r _{DS(ON)}	V _{GS} =1.8V, I _D =50mA		1.6	2.3	Ω
r _{DS(ON)}	V _{GS} =2.5V, I _D =50mA		1.3	1.9	Ω
r _{DS(ON)}	V _{GS} =5.0V, I _D =50mA		1.1	1.5	Ω
g _{FS}	V _{DS} =10V, I _D =200mA	200			mS
C _{rss}	V _{DS} =25V, V _{GS} =0, f=1.0MHz			5.0	pF
C _{iss}	V _{DS} =25V, V _{GS} =0, f=1.0MHz			50	pF
C _{oss}	V _{DS} =25V, V _{GS} =0, f=1.0MHz			25	pF

ELECTRICAL CHARACTERISTICS - D1: (T_A=25°C)

I _R	V _R =10V			20	μA
I _R	V _R =30V			100	μA
BV _R	I _R =500μA	40			V
V _F	I _F =100μA			0.13	V
V _F	I _F =1.0mA			0.21	V
V _F	I _F =10mA			0.27	V
V _F	I _F =100mA			0.35	V
V _F	I _F =500mA			0.47	V
C _T	V _R =1.0V, f=1.0MHz			50	pF

SOT-563 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B		0.008		0.20
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E		0.020		0.50
F	0.061	0.067	1.55	1.70
G		0.047		1.20
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

LEAD CODE:

- 1) Gate Q1
- 2) Source Q1
- 3) Cathode D1
- 4) Anode D1
- 5) Anode D1
- 6) Drain Q1

MARKING CODE: C35

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